

ABSTRACT

A first semiconductor layer that makes a capacitance coupling with a gate electrode of a thin film transistor through a gate insulating layer and a second semiconductor layer that makes a capacitance coupling with a storage capacitor line of a storage capacitor through the gate insulating layer are formed separately. Also, the first semiconductor layer and the second semiconductor layer are connected by a metal wiring. The gate electrode of the thin film transistor makes capacitance coupling with the first semiconductor layer and the storage capacitor line of the storage capacitor makes capacitance coupling with the second semiconductor layer independently. Voltage are induced in the first semiconductor layer and the second semiconductor layer independently. Since there will be no big discrepancy in voltage in the gate insulating layer, the dielectric break down and the leakage can be prevented.